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The NL27WZ16 is a high performance dual buffer operating from a 1.65 V to 5.5 V Supply.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 2.4 ns t_{PD} at $V_{CC} = 5 V (Typ)$
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Sink 32 mA at 4.5 V
- Available in SC-88, SC-74 and UDFN6 Packages
- Chip Complexity < 100 FETs
- -Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

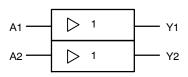


Figure 1. Logic Symbol

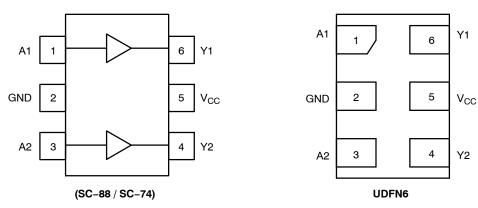
DATA SHEET www.onsemi.com

		MARKING DIAGRAMS
Ŵ	SC-88 DF SUFFIX CASE 419B-02	6 XXXM• 0 • 1
FR	SC-74 CASE 318F-05	XXX M• 0 • 1 0 0
	UDFN6 1.2x1.0, 0.4P CASE 517AA	× M
*	UDFN6 1.45x1.0, 0.5P CASE 517AQ	×M ●
*	UDFN6 1x1, 0.35P CASE 517BX	1 • X M
X, M	XXX = Specific Device = Date Code* = Pb-Free Packa	
(Not	e: Microdot may be in eit	her location)
*Date C depend	ode orientation and/or po ding upon manufacturing	osition may vary location.

ORDERING INFORMATION See detailed ordering and shipping information in the package

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

NL27WZ16





PIN ASSIGNMENT

Pin	Function
1	A1
2	GND
3	A2
4	Y2
5	V _{CC}
6	Y1

FUNCTION TABLE

A Input	Y Output
L	L
Н	Н

MAXIMUM RATINGS

Symbol	Characteristics	i	Value	Units
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V
V _{IN}	DC Input Voltage		–0.5 to +6.5	V
V _{OUT}	DC Output Voltage SC-88, SC-74, UDFN6	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	$\begin{array}{c} -0.5 \text{ to } V_{CC} + 0.5 \\ -0.5 \text{ to } + 6.5 \\ -0.5 \text{ to } + 6.5 \end{array}$	V
I _{IK}	DC Input Diode Current, V _{IN} < GND		-50	mA
I _{ОК}	DC Output Diode Current, V _{OUT} < GND		-50	mA
I _{OUT}	DC Output Source/Sink Current		±50	mA
$I_{\rm CC} {\rm or} I_{\rm GND}$	DC Supply Current per Supply Pin or Ground Pin		±100	mA
T _{STG}	Storage Temperature Range		–65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 secs		260	°C
TJ	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 2)	SC-88 SC-74 UDFN6	377 320 154	°C/W
PD	Power Dissipation in Still Air	SC-88 SC-74 UDFN6	332 390 812	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flamebility Rating	Oxygen Index: 28 to 34	UL 94-V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model (NLV) Charged Device Model	2000 1000 N/A	V
ILATCHUP	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.Applicable to devices with outputs that may be tri-stated.

Applicable to devices with outputs that may be in-stated, using 10 mm-by-1 inch, 2 ounce copper trace no air flow per JESD51-7.
 HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.

4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Para	Min	Мах	Unit	
V _{CC}	Positive DC Supply Voltage		1.65	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	V
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Transition Rise or Fall Rate	$\begin{array}{l} V_{CC} = 1.65 \; V \; to \; 1.95 \; V \\ V_{CC} = 2.3 \; V \; to \; 2.7 \; V \\ V_{CC} = 3.0 \; V \; to \; 3.6 \; V \\ V_{CC} = 4.5 \; V \; to \; 5.5 \; V \end{array}$	0 0 0 0	20 20 10 5	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{cc}			C	–55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Units
VIH	High-Level Input		1.65 to 1.95	0.65 x V _{CC}			$0.65 \times V_{CC}$		V
	Voltage		2.3 to 5.5	0.70 x V _{CC}			$0.70 \times V_{CC}$		
VIL	Low-Level Input		1.65 to 1.95			0.35 x V _{CC}		0.35 x V _{CC}	V
	Voltage		2.3 to 5.5			$0.30 \times V_{CC}$		0.30 x V _{CC}	
V _{OH}	High-Level Output Voltage	$ \begin{array}{l} V_{IN} = V_{IH} \text{ or } V_{IL} \\ I_{OH} = -100 \ \mu A \\ I_{OH} = -4 \ m A \\ I_{OH} = -8 \ m A \\ I_{OH} = -12 \ m A \\ I_{OH} = -16 \ m A \\ I_{OH} = -24 \ m A \\ I_{OH} = -32 \ m A \end{array} $	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	V _{CC} 1.4 2.1 2.4 2.7 2.5 4.0		V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8		V
V _{OL}	Low-Level Output Voltage	$ \begin{array}{l} V_{IN} = V_{IH} \text{ or } V_{IL} \\ I_{OL} = 100 \ \mu\text{A} \\ I_{OL} = 4 \ m\text{A} \\ I_{OL} = 8 \ m\text{A} \\ I_{OL} = 12 \ m\text{A} \\ I_{OL} = 16 \ m\text{A} \\ I_{OL} = 24 \ m\text{A} \\ I_{OL} = 32 \ m\text{A} \end{array} $	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5		- 0.08 0.2 0.22 0.28 0.38 0.42	0.1 0.24 0.3 0.4 0.4 0.55 0.55		0.1 0.24 0.3 0.4 0.55 0.55	V
I _{IN}	Input Leakage Current	V_{IN} = 5.5 V or GND	1.65 to 5.5	-	-	±0.1	-	±1.0	μA
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	-	-	1.0	-	10	μA
I _{CC}	Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5	-	-	1.0	-	10	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

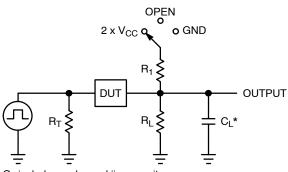
AC ELECTRICAL CHARACTERISTICS

				T _A = 25°C		$-40^{\circ}C \le T_A \le 85^{\circ}C$		$-55^{\circ}C \le T_A \le 125^{\circ}C$				
Symbol	Parameter	Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit	
t _{PLH} , Propagation t _{PHL} Delay, A to Y	$RL = 1 M\Omega$, CL = 15 pF	1.65 to 1.95	-	8.0	9.6	-	10.2	-	10.2	ns		
	CL = 15 RL = 50		$RL = 1 M\Omega$,	2.3 to 2.7	-	3.0	5.2	-	5.8	-	5.8	
		6L = 15 pF	3.0 to 3.6	-	2.3	3.6	-	4.0	-	4.0		
			4.5 to 5.5	-	1.8	2.9	-	3.2	-	3.2		
		RL = 500 Ω,	3.0 to 3.6	-	3.0	4.6	-	5.1	-	5.1		
		CL = 50 pF	4.5 to 5.5	-	2.4	3.8	-	4.2	-	4.2		

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V_{CC} = 5.5 V, V_{I} = 0 V or V_{CC}	2.5	pF
C _{OUT}	Output Capacitance	V_{CC} = 5.5 V, V_{I} = 0 V or V_{CC}	4.0	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V_{CC} = 3.3 V, V_{IN} = 0 V or V_{CC} 10 MHz, V_{CC} = 5.0 V, V_{IN} = 0 V or V_{CC}	11 12.5	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in}$) I_{CC} . C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in}$) $I_{CC} \cdot V_{CC}$.

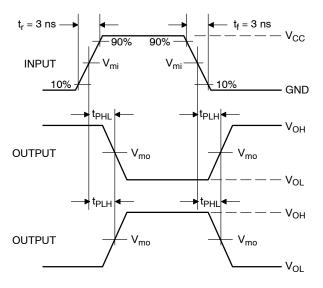


Test	Switch Position	C _L , pF	R_{L}, Ω	R_1, Ω	
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table			
t _{PLZ} / t _{PZL}	$2 \times V_{CC}$	50	500	500	
t_{PHZ} / t_{PZH}	GND	50	500	500	
X D 110					

X = Don't Care

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$ f = 1 MHz

Figure 3. Test Circuit



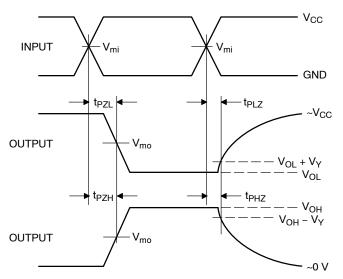


Figure 4. Switching Waveforms

		Vm		
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ}	V _Y , V
1.65 to 1.95	V _{CC} /2	V _{CC} /2	V _{CC} / 2	0.15
2.3 to 2.7	V _{CC} /2	V _{CC} /2	V _{CC} / 2	0.15
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} / 2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} / 2	0.3

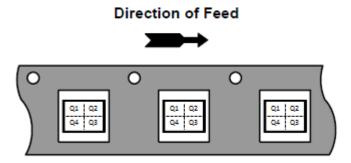
ORDERING INFORMATION

Device	Package	Specific Device Code	Pin1 Orientation (See bellow)	Shipping [†]
NL27WZ16DFT2G	SC-88	MR	Q4	3000 / Tape & Reel
NL27WZ16DFT2G-Q*	SC-88	MR	Q4	3000 / Tape & Reel
NL27WZ16DBVT1G	SC-74	MR	Q4	3000 / Tape & Reel
NL27WZ16MU1TCG	UDFN6, 1.45 x 1.0, 0.5P	F (Rotated 90° CW)	Q4	3000 / Tape & Reel
NL27WZ16MU3TCG	UDFN6, 1.0 x 1.0, 0.35P	T (Rotated 90° CW)	Q4	3000 / Tape & Reel
NL27WZ16MU2TCG	UDFN6, 1.2 x 1.0, 0.4P	5 (Rotated 180° CW)	Q4	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*-Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

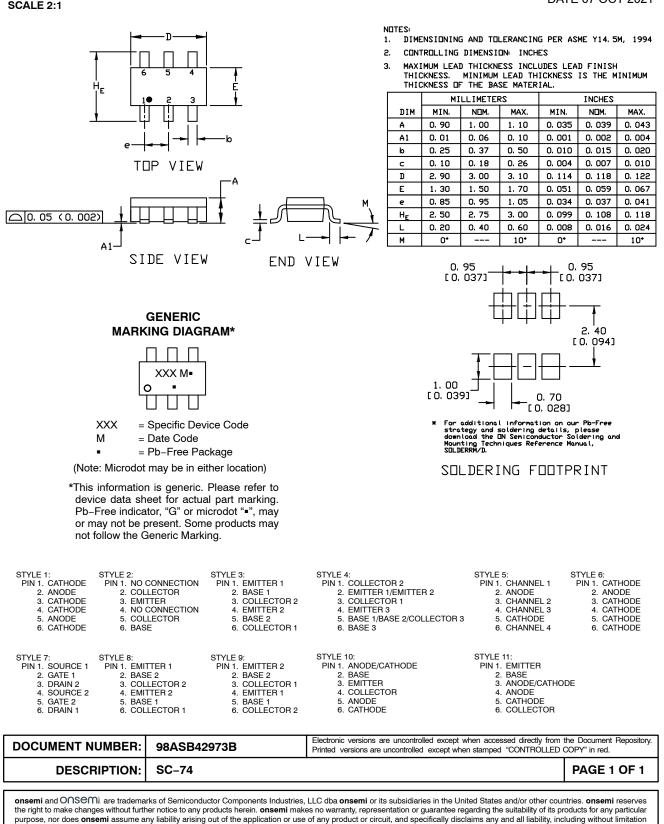
Pin 1 Orientation in Tape and Reel



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SC-74 CASE 318F ISSUE P

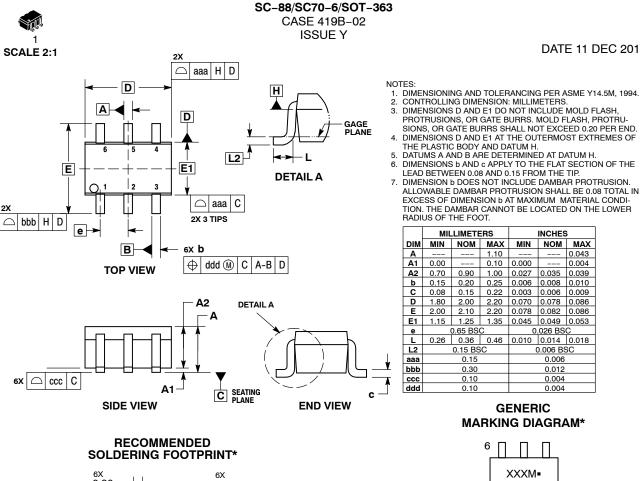
DATE 07 OCT 2021



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DATE 11 DEC 2012



6X 0.30 0.66 2 50 0.65 PITCH DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRU-SIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
- SIONS, OH GATE BUHHS SHALL NOT EXCEED 0.20 PEH END. DIMENSIONS D AND ET AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H. DATUMS A AND B ARE DETERMINED AT DATUM H. DIMENSIONS 5 AND 6 APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α			1.10			0.043	
A1	0.00		0.10	0.000		0.004	
A2	0.70	0.90	1.00	0.027	0.035	0.039	
b	0.15	0.20	0.25	0.006	0.008	0.010	
С	0.08	0.15	0.22	0.003	0.006	0.009	
D	1.80	2.00	2.20	0.070	0.078	0.086	
Е	2.00	2.10	2.20	0.078	0.082	0.086	
E1	1.15	1.25	1.35	0.045	0.049	0.053	
е		0.65 BS	С	0.026 BSC			
L	0.26	0.36	0.46	0.010	0.014	0.018	
L2	0.15 BSC			(0.006 BS	SC	
aaa	0.15			0.006			
bbb	0.30			0.012			
ccc		0.10		0.004			
ddd		0.10			0.004		

GENERIC **MARKING DIAGRAM***



XXX = Specific Device Code

- Μ = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE Y

DATE 11 DEC 2012

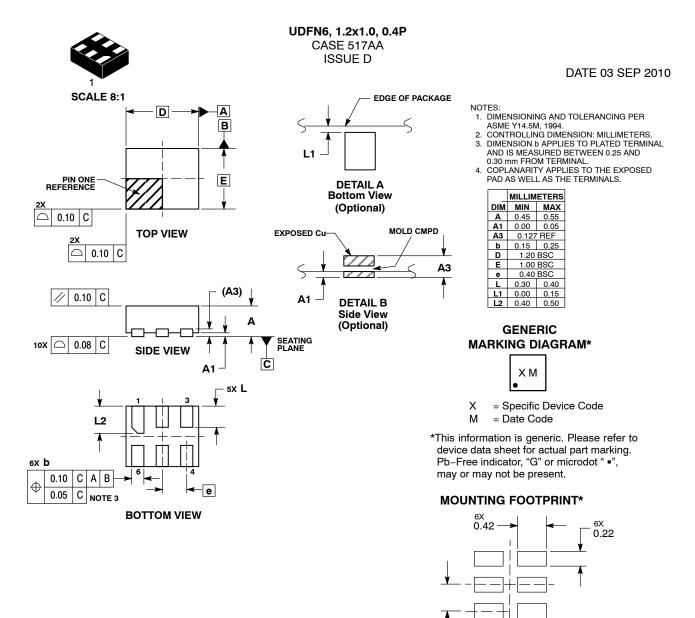
STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13:	STYLE 14:	STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:
PIN 1. ANODE	PIN 1. VREF	PIN 1. ANODE 1	PIN 1. BASE 1	PIN 1. BASE 1	PIN 1. VIN1
2. N/C	2. GND	2. ANODE 2	2. EMITTER 2	2. EMITTER 1	2. VCC
3. COLLECTOR	3. GND	3. ANODE 3	3. COLLECTOR 2	3. COLLECTOR 2	3. VOUT2
4. EMITTER	4. IOUT	4. CATHODE 3	4. BASE 2	4. BASE 2	4. VIN2
5. BASE	5. VEN	5. CATHODE 2	5. EMITTER 1	5. EMITTER 2	5. GND
6. CATHODE	6. VCC	6. CATHODE 1	6. COLLECTOR 1	6. COLLECTOR 1	6. VOUT1
STYLE 19:	STYLE 20:	STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:
PIN 1. I OUT	PIN 1. COLLECTOR	PIN 1. ANODE 1	PIN 1. D1 (i)	PIN 1. Vn	PIN 1. CATHODE
2. GND	2. COLLECTOR	2. N/C	2. GND	2. CH1	2. ANODE
3. GND	3. BASE	3. ANODE 2	3. D2 (i)	3. Vp	3. CATHODE
4. V CC	4. EMITTER	4. CATHODE 2	4. D2 (c)	4. N/C	4. CATHODE
5. V EN	5. COLLECTOR	5. N/C	5. VBUS	5. CH2	5. CATHODE
6. V REF	6. COLLECTOR	6. CATHODE 1	6. D1 (c)	6. N/C	6. CATHODE
STYLE 25:	STYLE 26:	STYLE 27:	STYLE 28:	STYLE 29:	STYLE 30:
PIN 1. BASE 1	PIN 1. SOURCE 1	PIN 1. BASE 2	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. SOURCE 1
2. CATHODE	2. GATE 1	2. BASE 1	2. DRAIN	2. ANODE	2. DRAIN 2
3. COLLECTOR 2	3. DRAIN 2	3. COLLECTOR 1	3. GATE	3. COLLECTOR	3. DRAIN 2
4. BASE 2	4. SOURCE 2	4. EMITTER 1	4. SOURCE	4. EMITTER	4. SOURCE 2
5. EMITTER	5. GATE 2	5. EMITTER 2	5. DRAIN	5. BASE/ANODE	5. GATE 1
6. COLLECTOR 1	6. DRAIN 1	6. COLLECTOR 2	6. DRAIN	6. CATHODE	6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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DIMENSIONS: MILLIMETERS

1.07

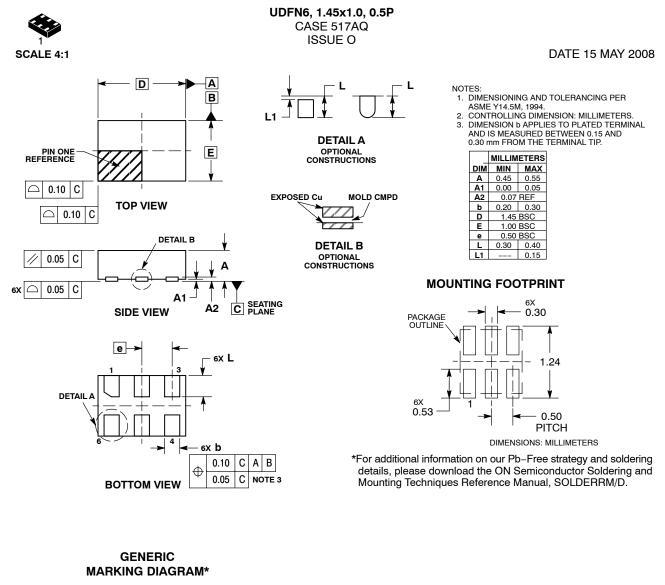
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

0.40

PITCH

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DESCRIPTION:	6 PIN UDFN, 1.2X1.0, 0.4P		PAGE 1 OF 1	
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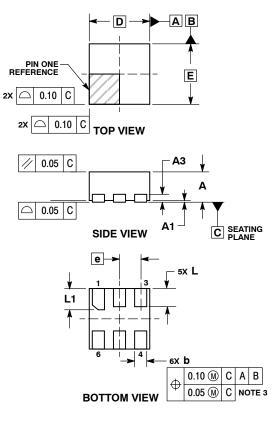
- X = Specific Device Code
- M = Date Code
- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

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DESCRIPTION:	UDFN6, 1.45x1.0, 0.5P		PAGE 1 OF 1	
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DUSem



SCALE 4:1



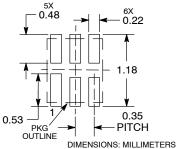
UDFN6, 1x1, 0.35P CASE 517BX **ISSUE O**

DATE 18 MAY 2011

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN A DE OR MULTICAL TERMINAL TR
- AND 0.20 MM FROM TERMINAL TIP.
 PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

BURRS AND MOLD FL				
	MILLIMETERS			
DIM	MIN MAX			
Α	0.45 0.55			
A1	0.00 0.05			
A3	0.13 REF			
b	0.12 0.22			
D	1.00 BSC			
Е	1.00 BSC			
е	0.35 BSC			
L	0.25 0.35			
L1	0.30 0.40			

RECOMMENDED **SOLDERING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC **MARKING DIAGRAM***



X = Specific Device Code M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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